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ABSTRACT

0046 A method for pre-etching a semiconductor wafer prior to a chemical mechanical polishing (CMP) process to achieve a uniform polishing rate including providing a wafer process surface having a layer of an oxide of a metal overlying said metal to be chemically mechanically polished; removing the layer of an oxide of the metal according to an etching process; cleaning the semiconductor wafer to include the wafer process surface according to a wet cleaning process; and, chemically mechanically polishing the wafer process surface according to a CMP process including applying at least an abrasive slurry to the wafer process surface.